

---

# HRW36F

Silicon Schottky Barrier Diode for High Frequency Rectifying

## HITACHI

ADE-208-160B (Z)

Rev. 2

Nov. 1994

---

### Features

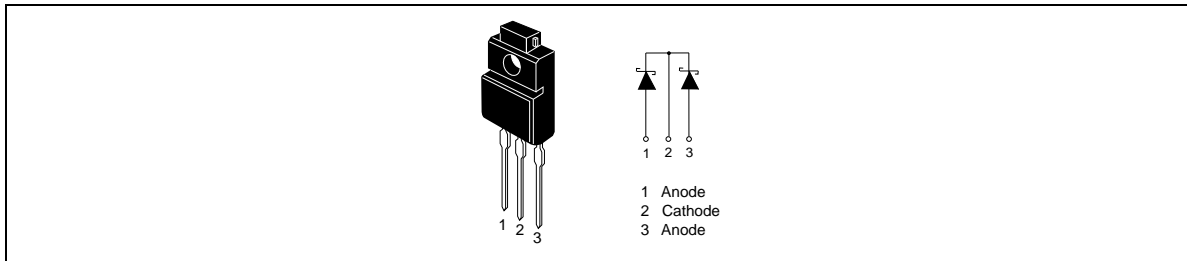
- Low forward voltage drop. ( $V_F = 0.80V$  max)
- High reverse voltage. ( $V_R = 90V$  max)
- Full molded fin enables easy insulation from heat sink.

### Ordering Information

Type No.	Laser Mark	Package Code
HRW36F	HRW36F	TO-220FM

---

### Pin Arrangement



# HRW36F

## Absolute Maximum Ratings (Ta = 25°C)\*<sup>1</sup>

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	90	V
Average forward current	$I_O^{*2}$	10	A
Non-Repetitive peak forward surge current	$I_{FSM}^{*3}$	70	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40 to +125	°C

- Notes: 1. Per one device  
 2. Square wave, Duty (1/2), Tc = 95°C, Sum of two devices  
 3. Half sine wave 10msec

## Electrical Characteristics (Ta = 25°C)\*

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_{F1}$	—	—	0.6	V	$I_F = 2.0A$
	$V_{F2}$	—	—	0.8		$I_F = 4.0A$
Reverse current	$I_R$	—	—	4.0	mA	$V_R = 90V$

Note: Per one device

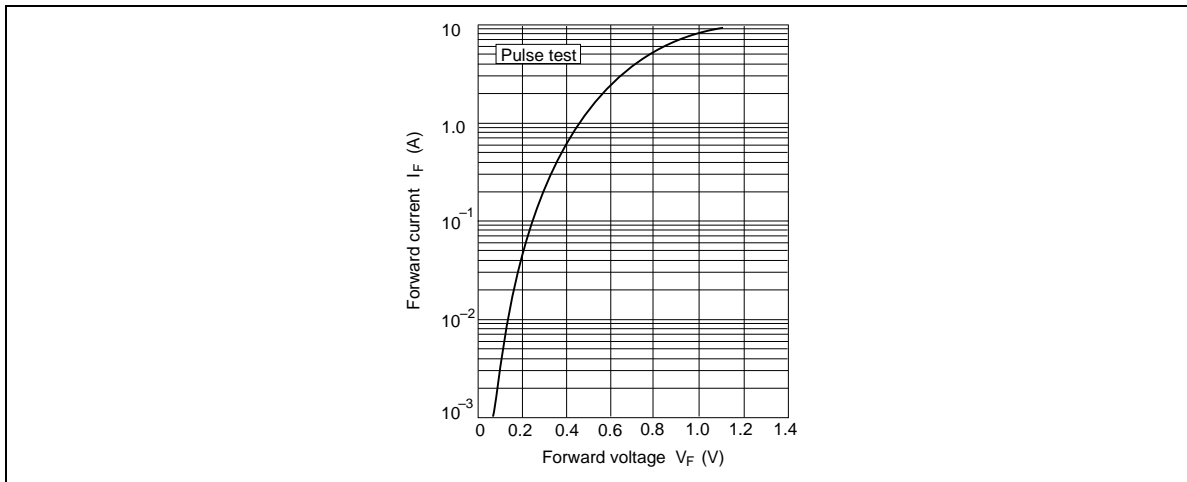


Fig.1 Forward current Vs. Forward voltage

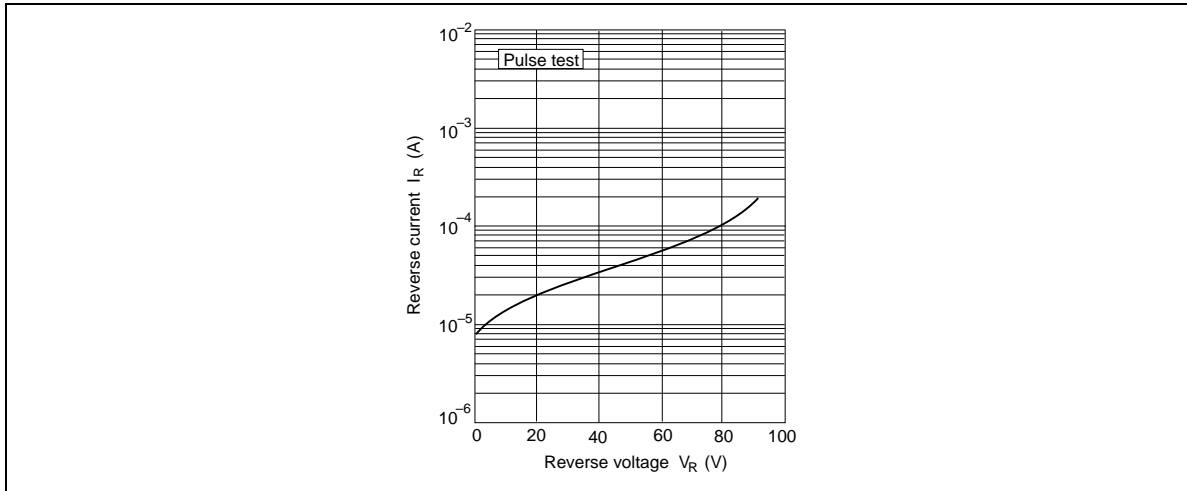


Fig.2 Reverse current Vs. Reverse voltage

Package Dimensions

